SELV TELECOMMUNICATION LINE OVERVOLTAGE PROTECTION

- **Digital Line Protection**
 - ISDN
 - xDSL
- Safety Extra Low Voltage, SELV, values

DEVICE	V _{DRM}	V _(BO)
'4030	± 15	± 30
'4040	± 25	± 40

High Current "H" Series for GR-1089-CORE

WAVE SHAPE	STANDARD	I _{TSP} A
10/1000 μs	GR-1089-CORE	100

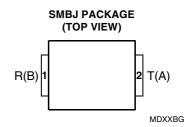
100 A to 75 A Functional Replacements for

DEVICE TYPE	FUNCTIONAL REPLACEMENT			
P0300SC	TISP4040H1BJ			
P0300SB	1137404011111			

description

These devices are designed to limit overvoltages on digital lines. Overvoltages are normally caused by a.c. power system or lightning flash disturbances which are induced or conducted on to the telephone line. A single device provides 2point protection and is typically used for the protection of transformer windings and low voltage electronics.

The protector consists of a symmetrical voltagetriggered bidirectional thyristor. Overvoltages are initially clipped by breakdown clamping until the voltage rises to the breakover level, which causes the device to crowbar into a low-voltage on state. This low-voltage on state causes the current resulting from the overvoltage to be safely diverted through the device. The device switches off when the diverted current subsides falls below the holding current value.



device symbol



Terminals T and R correspond to the alternative line designators of A and B



TISP4030H1BJ, TISP4040H1BJ **EXPERIMENTAL SAMPLE DATA** BIDIRECTIONAL OVERVOLTAGE PROTECTORS AUGUST 1999 - REVISED MARCH 2000

absolute maximum ratings, T_A = 25 °C (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (T _J = 25 °C)		V_{DRM}	±15 ± 25	٧
Non-repetitive peak on-state pulse current (see Notes 1 and 2) 10/1000 µs (Telcordia GR-1089-CORE, 10/1000 µs voltage wave shape)	'4040H1BJ	I _{TSP}	± 25 ± 100	А
Non-repetitive peak on-state current (see Notes 1 and 2), 0.2 s 50 Hz a.c. 2 s 50 Hz a.c.		I _{TSM}	25 12	А
Maximum junction temperature		T_JM	150	°C
Storage temperature range		T _{stg}	-65 to +150	°C

NOTES: 1. Initially the device must be in thermal equilibrium with T_J = 25 °C.

electrical characteristics for the R and T terminals, $\rm T_A$ = 25 $^{\circ} C$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{DRM}	Repetitive peak off-state current	$V_D = V_{DRM}$			± 10	μΑ
V _(BO) Breakover voltage	Proakovor voltago	$dv/dt = \pm 250 \text{ V/ms}, R_{SOURCE} = 300 \ \Omega$			± 30	V
	breakover voltage				± 40	v
I _(BO)	Breakover current	$dv/dt = \pm 250 \text{ V/ms}, R_{SOURCE} = 300 \Omega$			± 0.8	Α
la.	Off-state current	$V_D = \pm 13 \text{ V}$ '4030H1BJ			± 2	μA
I _D Off-state current	$V_D = \pm 22 \text{ V}$ '4040H1BJ			± 2	μΛ	
1	Holding current	$I_T = \pm 5 \text{ A, di/dt} = +/-30 \text{ mA/ms}$ (4030H1BJ)		± 0.05		Α
I _H Holding	riolaling carretit	17 – ±5 A, di/dt – +7-50 MA/MS		± 0.05		Α
C	Off-state capacitance	$f = 1 \text{ MHz}, V_d = 1 \text{ Vrms}, V_D = 1 \text{ V},$ '4030H1BJ		95		pF
C _{off}	On-State Capacitance	'4040H1BJ		95		ρΓ

thermal characteristics

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JL}$	Junction to leads thermal resistance				20	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance				100	°C/W



^{2.} The surge may be repeated after the device returns to its initial conditions.

PARAMETER MEASUREMENT INFORMATION

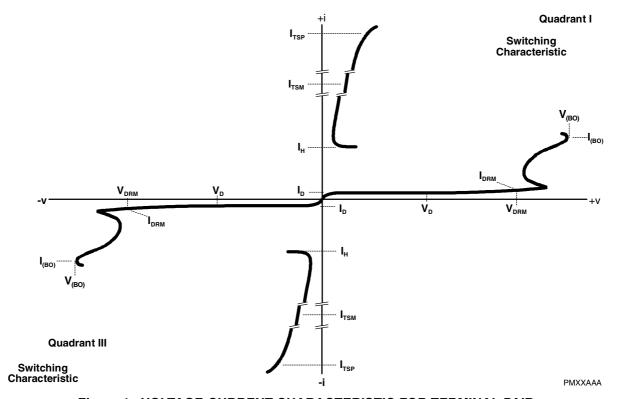


Figure 1. VOLTAGE-CURRENT CHARACTERISTIC FOR TERMINAL PAIR

T and R measurements are referenced to the R terminal



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DEVICE STATUS

samples

The current samples of the TISP4030H1BJ and TISP4040H1BJ are experimental units and have only been verified for a surge rating of ± 100 A, 10/1000. These samples are suitable for circuit evaluation by customers and should not be used for long term reliability testing. It is considered that the small signal electrical circuit performance of these samples is reasonably representative of a final production design.

It is intended that the final production parts of the TISP4030H1BJ and TISP4040H1BJ will use a modified chip design.



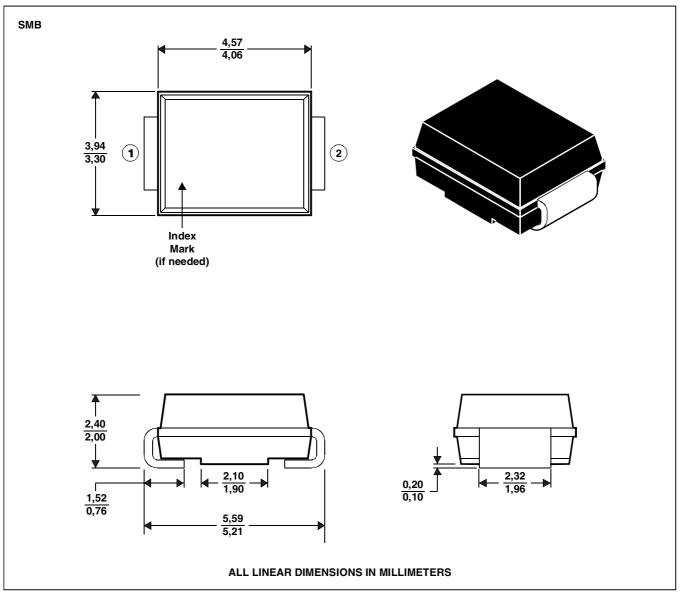
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MECHANICAL DATA

SMBJ (DO-214AA)

plastic surface mount diode package

This surface mount package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



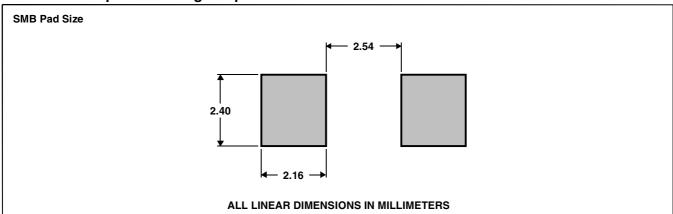
MDXXBHA



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MECHANICAL DATA

recommended printed wiring footprint.

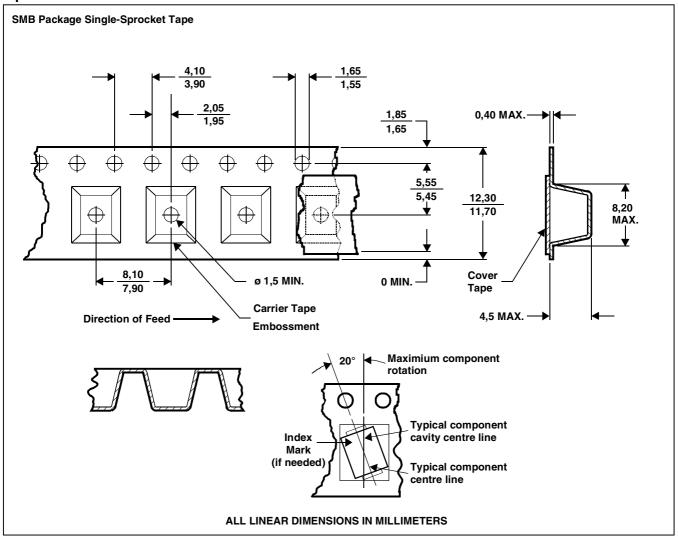


MDXXBI



MECHANICAL DATA

tape dimensions



NOTES: A. The clearance between the component and the cavity must be within 0,05 mm MIN. to 0,65 mm MAX. so that the component cannot rotate more than 20° within the determined cavity.

MDXXBJ

B. Taped devices are supplied on a reel of the following dimensions:-

Reel diameter: $330 \pm 3.0 \text{ mm}$ Reel hub diameter 75 mm MIN. Reel axial hole: $13.0 \pm 0.5 \text{ mm}$

C. 3000 devices are on a reel.



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